

✓ 2814#

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : H. Zhang
Serial No.: 09/362,808
Filed : July 28, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Art Unit : 2814
Examiner : Thanh V. Tran

Commissioner for Patents
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

FEB 22 2002

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TRANSMITTAL LETTER AND PETITION FOR AUTOMATIC EXTENSION

Correspondence relating to this application is enclosed.
The required fees are computed below. Please apply any charges
not covered, or any credits, to Deposit Account No. 06-1050.

Total Claims	40	-	37	=	3	\$54
Independent	6	-	6	=	0	\$0


TOTAL FEE DUE \$54

A check for \$54 is attached.

Respectfully submitted,

Date:

8/5/08



Scott C. Harris
Reg. No. 32,030

Fish & Richardson P.C.
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February 5, 2002

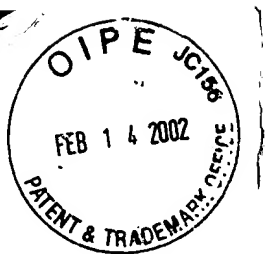
Date of Deposit

Signature



Susan Regan

Typed or Printed Name of Person Signing Certificate



Attorney's Docket No.: 07977/088002/US3155D1

#10D
R. K. K. K.
2/26/2002

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AMENDMENT

Sir:

In response to the Official Action mailed November 5, 2001, Paper No. 9, in the above-referenced application, please amend the above-identified application as follows.

In the Claims:

Please amend claims 1, 2, 10, 14, 19, and 24 as follows:

sub
EX
DI

1. (Amended) A semiconductor device comprising:
a semiconductor having at least channel, source and drain regions;
an insulating film formed on said semiconductor;
a first interlayer insulating film over said insulating film;

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Susan Regan

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